Notice of References Cited Application/Control No. 10/063,626 Examiner Ayal I. Sharon Applicant(s)/Patent Under Reexamination HUANG, ANDY Art Unit Page 1 of 2

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-6,928,626	08-2005	McGaughy et al.	716/1
	В	US-6,931,609	08-2005	Naruta et al.	716/4
	С	US-			
	D	US-			" -
	E	US-			,
	F	US-			
	G	US-			
	Н	US-			
	1	US-			
	J	US-			
	К	US-			,
	L	US-	4		
	M,	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
	Q					
	R					
	s					
	Т					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Hamoui, A.A. et al. "An Analytical Model for Current, Delay, and Power Analysis of Submicron CMOS Logic Circuits." IEEE Transactions on Circuits and Systems II: Analog and Digital DSP. Oct. 2000. Vol. 47, Issue 10, pp. 999-1007.
	٧	"Level 27 SOSFET Model." Star-Hspice Manual – Release 1999.4 Dec. 15, 1999. Printed from http://siloam.han.ac.kr/~young/data/hspice_html/hspice-152.html.
	w	Alinikula, P. et al. "Design of Class E Power Amplifier with Non-linear Parasitic Output Capacitance." IEEE Transactions on Circuits and Systems II: Analog and Digital DSP. Feb. 1999. Vol. 46, Issue 2, pp. 114-119.
	x	Ma, S.W. et al. "Piece-Wise Linear Approximation of MOS Nonlinear Junction Capacitance in High-Frequency Junction Capacitance in High-Frequency Class E Amplifier Design." 2003 IEEE Conf. on Electron Device and Solid-State Circuits. Dec. 16-18, 2003. pp

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

Notice of References Cited Application/Control No. 10/063,626 Examiner Ayal I. Sharon Applicant(s)/Patent Under Reexamination HUANG, ANDY Page 2 of 2

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-			
	В	US-			
	С	US-			
	D	US-			
	E	US-			·
	F	US-			
	G	US-			
	I	US-			
	_	US-			
	J	US-			
	κ	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
	Q					
	R					
	s					
	Т	_				

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Enz, C. "An MOS Transistor Model for RF IC Design Valid in All Regions of Operation." IEEE Transactions on Microwave Theory and Techniques. Jan. 2002. Vol.50, Issue 1. pp.342-359.
	V	Bisdounis, L. "Analytical Transient Response and Propagation Delay Evaluation of the CMOS Inverter for Short-Channel Devices." IEEE Journal of Solid State Circuits. Feb. 1998, Vol.33, Issue 2, pp.302-306.
	w	Ismail, M. et al. "Finite GB and MOS Parasitic Capacitance Effects in a Class of MOSFET-C Filters." Proc. of the 33rd Midwest Symposium on Circuits and Systems. Aug.12-14, 1990. Vol.2, pp.938-941.
	x	Boothroyd, A.R. et al. "MISNAN – A Physically Based Continuous MOSFET Model for CAD Applications." IEEE Transactions on CAD of Integrated Circuits and Systems. Dec. 1991. Vol.10, Issue 12. pp.1512-1529.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYYY format are publication dates. Classifications may be US or foreign.